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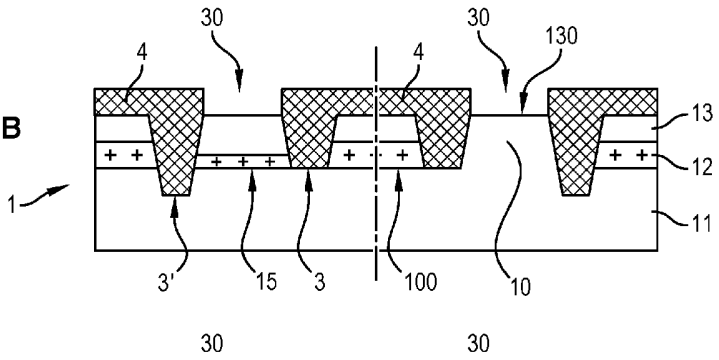
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(54) **Title**: METHOD FOR MANUFACTURING COMPONENTS

FIG. 6B



(57) **Abstract**: The invention relates to a method for manufacturing components on a mixed substrate. It comprises the following steps: providing a substrate (1) of the semiconductor-on-insulator (SeOI) type comprising a buried oxide layer (12) between a supporting substrate (11) and a thin layer (13), forming in this substrate (1) a plurality of trenches (3, 3') opening out at the free surface (130) of said thin layer (13) and extending over a depth such that it passes through said thin layer (13) and said buried oxide layer (12), these primary trenches (3, 3') delimiting at least one island (30) of said SeOI substrate (1), forming a mask (4) inside said primary trenches (3, 3') and as a layer covering the areas of the free surface (130) of said thin layer (13) located outside said islands (30), proceeding with heat treatment for dissolving the buried oxide layer present at said island (30), so as to reduce the thickness thereof.

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